

Amendments to the Claims:

Claims 1, 3, 4, 6, and 7 have been amended herein. Please note that all claims currently pending and under consideration in the referenced application are shown below. Please enter these claims as amended. This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

1. (Currently Amended) A method of forming a semiconductor device assembly, said method comprising:

providing a substrate having an upper surface and a lower surface;

depositing a layer of copper on the upper surface and the lower surface of the substrate;

patterning the layer of copper on at least the one surface of the upper surface and the lower

surface of the substrate to form at least one bond pad thereon;

depositing at least one layer of metal on at least a portion of the layer of copper;

connecting one end of a conductive lead of a TAB tape to the at least one layer of metal; and

consuming a portion of the at least one layer of metal during the connecting of one end of a

conductive lead of a TAB tape for connecting at least a portion of one end of the conductive lead
of the TAB tape to at least a portion of the layer of copper.

2. (Previously Presented) The method of claim 1, further comprising:

connecting one end of the conductive lead of the TAB tape to the at least one layer of metal using

a wire bond.

3. (Currently Amended) A method of forming a semiconductor device assembly, said method comprising:

providing a substrate having an upper surface and a lower surface;

depositing a layer of copper on the upper surface and the lower surface of the substrate;

patterning the layer of copper on both the upper surface and the lower surface of the substrate to form at least one bond pad thereon;
depositing at least one layer of gold metal on at least a portion of the layer of copper;
connecting one end of a conductive lead of a TAB tape to the at least one layer of gold metal; and consuming a portion of the at least one layer of metal during the connecting of one end of a conductive lead of a TAB tape for connecting at least a portion of one end of the conductive lead of the TAB tape to at least a portion of the layer of copper.

4. (Currently Amended) A method of forming a semiconductor device assembly having a substrate having an upper surface and a lower surface, said method comprising:
depositing a layer of copper on the upper surface and the lower surface of the substrate;
patterning the layer of copper on ~~one surface of~~ the upper surface and the lower surface of the substrate to form at least one bond pad thereon;
depositing at least one layer of metal on at least a portion of the layer of copper;
connecting one end of a conductive lead of a TAB tape to the at least one layer of metal; and consuming a portion of the at least one layer of metal during the connecting of one end of a conductive lead of a TAB tape for connecting at least a portion of one end of the conductive lead of the TAB tape to at least a portion of the layer of copper.

5. (Previously Presented) The method of claim 4, further comprising:
connecting one end of the conductive lead of the TAB tape to the at least one layer of metal using a wire bond.

6. (Currently Amended) A method of forming a semiconductor device assembly having a substrate having an upper surface and a lower surface, said method comprising:
depositing a layer of copper on more than one surface of the upper surface and the lower surface of the substrate;
patterning the layer of copper on the upper surface and the lower surface of the substrate to form at least one bond pad thereon;

depositing at least one layer of gold metal on at least a portion of the layer of copper; connecting one end of a conductive lead of a TAB tape to the at least one layer of gold metal; and consuming a portion of the at least one layer of metal during the connecting of one end of a conductive lead of a TAB tape for connecting at least a portion of one end of the conductive lead of the TAB tape to at least a portion of the layer of copper.

7. (Currently Amended) A method of forming a semiconductor device assembly having a substrate having an upper surface and a lower surface, said method comprising: depositing a layer of copper on more than one desired surface of one surface of the upper surface and the lower surface of the substrate; patterning the layer of copper on at least one surface of the upper surface and the lower surface of the substrate to form at least one bond pad thereon; depositing at least one layer of gold metal on at least a portion of the layer of copper; connecting one of an end of a conductive lead of a TAB tape and a portion of a bond wire to the at least one layer of gold metal; and consuming a portion of the at least one layer of metal during the connecting of one end of a conductive lead of a TAB tape for connecting at least a portion of one end of the conductive lead of the TAB tape to at least a portion of the layer of copper.